

**In the Claims**

1. (amended) A method of forming a capacitor construction, comprising:  
providing a first capacitor electrode;  
forming a perovskite-type dielectric material over the first capacitor electrode, the perovskite-type dielectric material having a first edge region proximate the first electrode and a portion further from the first electrode than the first edge region, said portion having a different amount of crystallinity than the first edge region; and  
while the first edge region and the portion differ in the amount of crystallinity relative to one another, forming a second capacitor electrode over the perovskite-type dielectric material.